Erratum

Erratum to: Electronic parameters for charge transfer along DNA

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In our discussion of electronic parameters for charge (hole or electron) transfer along DNA we have omitted to mention that, regarding the tight-binding description of hole transport, the corresponding tight-binding parameters should be taken with the opposite sign of the calculated on-site energies and transfer hopping integrals. This means that for describing hole transport at the base-pair level, the on-site energies E_{H}^{bp} presented in the second row of table 2 and the hopping transfer integrals t_{H}^{bp} presented in the second column of table 3 should be used with opposite signs in order to provide the tight-binding parameters of eq. (10). Similarly, for describing hole transport at the single-base level, the on-site energies E_{H}^{b} presented in the eleventh row of table 1 and the hopping transfer integrals t_{H}^{b} presented in the second column of tables 4–7 should be used with opposite signs in order to provide the tight-binding parameters of eq. (13).

Moreover, on p. 300, 8 lines below eq. (14), in the calculation of charge transfer hopping parameters the separation between adjacent base-pairs in B-DNA should read 3.4 Å, instead of 3.14 Å.

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